# IC for Headphone Stereos Monolithic IC MM1104

August 6, 1994

#### Outline

This IC was developed for use in 3 V headphone stereos. It incorporates all the basic functions of tape players.

Mitsumi has previously offered the LAG665, LAG668, LAG673 and MM1006 as one-chip versions. However, this IC is the result of a through review and redesign extending to circuit details.

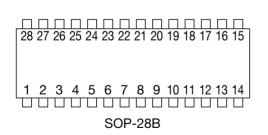
#### Features

- 1. Configuration: Pre-and power amp, motor control
- Adoption of shock noise prevention circuitry Through the use of a circuit which suppresses noise occurring when the power supply is turned on and off, noise output is reduced without muting.
- Stable motor speed control circuit
  A bridge circuit employing power transistors provides motor speed control with minimal drift.
- 4. Preamp off pin is convenient for radio connections
- 5. Radiation pin: When radio wave-induced noise is a problem, this pin can be used to cut the frequency characteristic.

#### Package

SOP-28B (MM1104AF, MM1104BF, MM1104CF)

## **Pin Assignment**



1	1/2Vcc	15	N.C
2	Prein1	16	Speed
3	NFB1	17	Phase
4	PreOUT1	18	Vs
5	Pre Off	19	PowerOUT2
6	Powerin1	20	Amp Vcc
7	Radiation1	21	Filter
8	PowerOUT1	22	Radiation2
9	GND	23	Powerin2
10	Governor Vcc	24	N.C
11	N.C	25	PreOUT2
12	PCOUT	26	NFB2
13	GND	27	Prein2
14	Governor GND	28	Amp GND

# Absolute Maximum Ratings

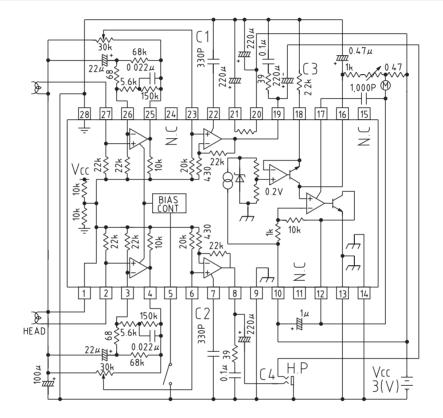
Item	Symbol	Ratings	Units	
Operating temperature	Topr	-20~+65	°C	
Storage temperature	Tstg	-40~+125	°C	
Power supply current	Vcc	-0.3~+7.5	V	
Power consumption	Pd	700 (Ta=25°C)	mW	
Operating voltage	Vop	+2.0~+5.0	V	

# Electrical Characteristics (Except where noted otherwise, Ta=25°C)

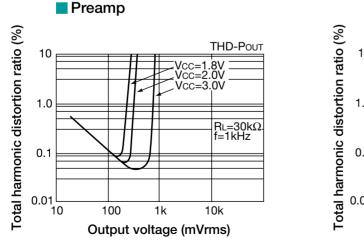
Item	Symbol	Measurement conditions	Min.	Тур.	Max.	Units		
Consumption current	Icc	Amp. only		11	18	mA		
Preamp unit (Ta=25°C)								
Open-circuit gain	GVo	Vo=-10dBm f=100Hz		86		dB		
Closed-circuit gain	osed-circuit gain GVc Vo=-10dBm			42		dB		
Maximum output voltage	Vom	THD=10%	0.5	0.74		Vrms		
Total harmonic distortion ratio	THD	Vo=-10dBm		0.06	0.5	%		
Output noise voltage	Vno	Rg=2.2kΩ, CCIR waiting		240	500	μVrms		
Crosstalk between channels	СНст	Vo=-10dBm		60		dB		
Ripple rejection	RR	Vcc=3V, VR=-20dBm, fr=100Hz	30	42		dB		
Output voltage with preamp off	VoOff	Vo=–10dBm, when pre operation		-100	-70	dBm		
Input resistance with preamp off	RiOff		7	10	13	kΩ		
Output resistance with preamp off	RoOff		7	10	13	kΩ		
Measurement conditions: Except where noted otherwise, Vcc=3V, Rg= $2.2k\Omega$ , RL= $30k\Omega$ , f= $1kHz$								
Power amp unit (Ta=25°C)								
Input resistance	Ri	i		20	26	kΩ		
Voltage gain	Voltage gainGvPo=5mW		32	34	36	dB		
Voltage gain difference between channels	⊿Gv			0	2	dB		
Maximum output power I	Pom1	THD=10%, RL=16Ω		62		mW		
Maximum output power II	Pom2	THD=10%, RL=32Ω		34		mW		
Total harmonic distortion ratio	harmonic distortion ratio THD Po=5mW			0.4	2	%		
Crosstalk between channels	СНст	Po=5mW	45	62		dB		
Output noise voltage	Vn	Rg=1kΩ, CCIR waiting		150	300	μVrms		
Ripple rejection	RR	Vcc=3V, Vr=-20dBm, fr=100Hz	40	50		dB		
Measurement conditions: Except where noted otherwise, Vcc=3V, Rg=1kΩ, RL=16Ω, f=1kHz								
Motor governor (Ta=25°C)								
Consumption current	Id	A2 measured		2.0	7.0	mA		
Startup current	Iмs	Ім measured when $Rv=1.5\Omega$	500			mA		
Reference voltage	Vref	V5 measured with SW12 off	0.09	0.10	0.11	V		
Reference voltage fluctuation I	⊿Vref1	VS fluctuation for		0.1	0.5	%/V		
		Vcc=1.5 to 3.5V, Vcc=3.0V ref.			0.0	707 V		
Reference voltage fluctuation II	⊿Vref2	VS fluctuation for	0.005		0.05	%/mA		
		Iм=25 to 200m A, Iм=100mA ref.			0.05	/0/ 11// 1		
Reference voltage fluctuation III	⊿Vref3	VS fluctuation for	0.01			%/°C		
		Ta= $-10$ to $60^{\circ}$ C, Ta= $25^{\circ}$ C ref.				/0/ C		
Output saturation voltage	VoSAT	Reference voltage V8 measured	0.2		0.3	V		
		IM=200mA with SW12 on		0.2		v		
Bridge ratio	K	V7/V6 measured	9	10	11			

Item	Symbol	Measurement conditions	Min.	Тур.	Max.	Units	
Bridge ratio fluctuation I	⊿K1	K fluctuation for		0.1	0.2	%/V	
Bhuge faile fluctuation f		Vcc=1.5 to 3.5V, Vcc=3.0V ref.					
Bridge ratio fluctuation II	⊿K2	K fluctuation for	0.05		0.2	%/mA	
bildge faile incluation if		IM=25 to 200m A, IM=100mA ref.		0.05	0.2	/0/ IIIA	
Bridge ratio fluctuation III	⊿K3	K fluctuation for		0.01		%/°C	
Bhuge ratio nuctuation in		Ta=-10 to 60°C, Ta=25°C ref.	0.01			/0/ C	
Measurement conditions: Except where noted otherwise, Vcc=3V, IM=100mA, SW11=OFF, SW12=ON							

## Block Diagram (Example of Application Circuits)



## Characteristics



Power amp

